STD888T4

Medium Current, High Performance, Low Voltage PNP Transistor

General features

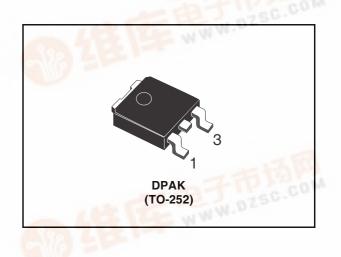
- Very low Collector to Emitter saturation voltage
- D.C. Current gain, h_{FE} >100
- 5A continuous collector current
- Surface mounting DPAK(TO-252) power package in tape & reel packing
- In compliance with the 2002/93/EC European Directive

Description

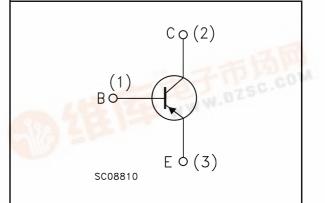
The device in manufactured in low voltage PNP Planar Technology by using a "Base Island" layout. The resulting transistor shows exceptional high gain performance coupled with very low saturation voltage.

Applications

- Power management in portable equipment
- Voltage regulation in bias supply circuits
- Switching regulator in battery charger applications
- Heavy load driver



Internal schematic diagram



Order codes

Part Number	Marking	Package	Packing
STD888T4	D888	DPAK	Tape & reel
I	- att	C COM	· · · ·



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1 Electrical ratings

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-base voltage (I _E = 0)	-45	V
V_{CEO}	Collector-emitter voltage ($I_B = 0$)	-30	V
V_{EBO}	Emitter-base voltage (I _C = 0)	-6	V
۱ _C	Collector current	-5	Α
I _{CM}	Collector peak current (t _P < 5ms)	-10	Α
P _{tot}	Total dissipation at $T_c = 25^{\circ}C$	15	W
T _{stg}	Storage temperature	-65 to 150	°C
ТJ	Max. operating junction temperature	150	°C

Table 1. Absolute maximum rating

Table 2. Thermal data

Symbol	Parameter	Value	Unit
R _{thj-case}	Thermal resistance junction-case max	8.33	°C/W

2 Electrical characteristics

($T_{case} = 25^{\circ}C$ unless otherwise specified)

i able 3.	Electrical characteristics					
Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
I _{CBO}	Collector cut-off current (I _E =0)	$V_{CB} = -30V$ $V_{CB} = -30V$; $T_{C} = 100^{\circ}C$			-10 100	μΑ μΑ
I _{EBO}	Emitter cut-off current (I _C =0)	V _{EB} = -6V			-10	μA
V _{(BR)CEO} ⁽²⁾	Collector-emitter breakdown voltage (I _B =0)	I _C = -10mA	-30			V
V _{(BR)CBO}	Collector-base breakdown voltage (I _E =0)	I _C = -100μΑ	-45			V
V _{(BR)EBO}	Emitter-base breakdown voltage (I _C =0)	I _E = -100μA	-6			V
V _{CE(sat)} ⁽²⁾	Collector-emitter saturation voltage	I _C = -0.5A I _B = -5mA			-0.15	V
CE(sat)		I _C = -2A I _B = -50mA			-0.35	V
	_	I _C = -5A I _B = -250mA			-0.7	V
		$I_{\rm C} = -6A$ $I_{\rm B} = -250 {\rm mA}$		-0.7		V
		$I_{\rm C} = -8$ $I_{\rm B} = -400$ mA		-1		V
		I _C = -10A I _B = -500mA		-1.2		V
V _{BE(sat)} ⁽²⁾	Base-emitter saturation voltage	I _C = -2A I _B = -50mA			-1.1	V
		$I_{\rm C} = -6A$ $I_{\rm B} = -250 {\rm mA}$		-1.2		V
		I _C = -10mA V _{CE} = -1V	120	200		
		I _C = -500mA V _{CE} = -1V	100	200	300	
	DC current gain	I _C = -5A V _{CE} = -1V	70	100		
h _{FE} ⁽²⁾		$I_{\rm C} = -5A$ $V_{\rm CE} = -1V$				
		$T_{\rm C} = 100^{\circ}{\rm C}$		100		
		$I_{\rm C} = -8$ A $V_{\rm CE} = -1$ V		55		
		$I_{\rm C} = -10A$ $V_{\rm CE} = -1V$		35		
t _d	Resistive load Delay time	$I_{\rm C} = -3A$ $V_{\rm CC} = -20V$	/	180	220	ns
t _r	Rise time	I _{B1 = -} I _{B2 =} -60mA		160	210	ns
t _s	Storage time	(see figure 7)		250	300	ns
t _f	Fall time			80	100	ns
1				50		10

Table 3.	Electrical	characteristics

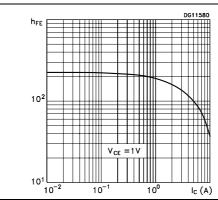
Note (2) Pulsed duration = 300 μ s, duty cycle \leq 1.5%

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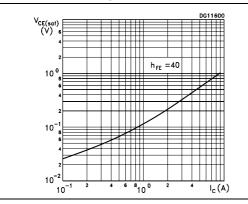
2.1 Electrical characteristics (curves)

Figure 1. DC current gain



 h_{FE} 10^{2} 10^{1} 10^{-2} 10^{-1} 10^{0} 10^{0} 10^{0} 10^{0} 10^{0} 10^{0} 10^{0} 10^{0} 10^{0} 10^{0} 10^{0} 10^{0} 10^{0} 10^{0} 10^{0} 10^{0} 10^{-1} 10^{0} 10^{0} 10^{-1} 10^{0} 10^{0} 10^{-1} 10^{0} 10^{-1} 10^{0} 10^{-1} 10^{0} 10^{-1} 10^{0} 10^{-1} 10^{-1} 10^{0} 10^{-1} $10^{$

Figure 3. Collector-emitter saturation Figure 4. Base-emitter saturation voltage voltage



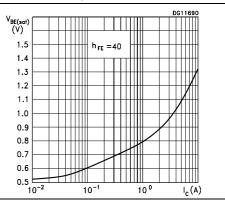


Figure 5. Switching time resistive load Figure 6. Switching time resistive load

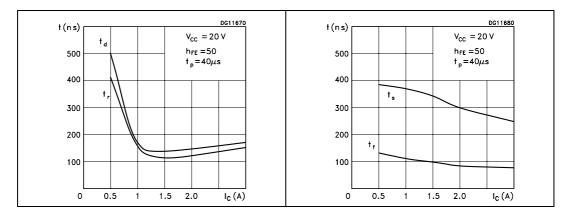
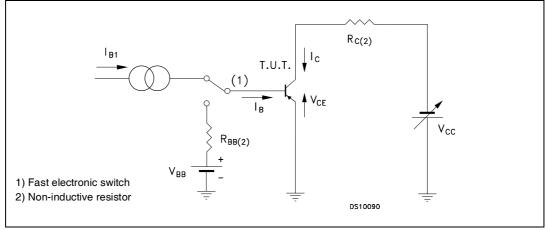


Figure 2. DC current gain

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2.2 Test circuits



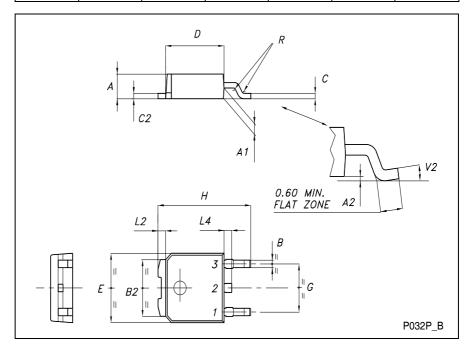


3 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com



	TO-252 (DPAK) MECHANICAL DATA					
DIM.	mm			inch		
Divi.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	2.20		2.40	0.087		0.094
A1	0.90		1.10	0.035		0.043
A2	0.03		0.23	0.001		0.009
В	0.64		0.90	0.025		0.035
B2	5.20		5.40	0.204		0.213
С	0.45		0.60	0.018		0.024
C2	0.48		0.60	0.019		0.024
D	6.00		6.20	0.236		0.244
E	6.40		6.60	0.252		0.260
G	4.40		4.60	0.173		0.181
н	9.35		10.10	0.368		0.398
L2		0.8			0.031	
L4	0.60		1.00	0.024		0.039
V2	0°		8°	0°		0°



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4 Revision history

Table 4.	Revision	history
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Date	Revision	Changes
24-Mar-2004	1	Initial release.
03-Apr-2006	2	New template.

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